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ZXTN19055DZ 55V, SOT89, NPN medium power transistor

Summary

 $BV_{CEX} > 150V$ $BV_{CEO} > 55V$ $I_{C(cont)} = 6A$ $V_{CE(sat)} < 60mV @ 1A$ $R_{CE(sat)} = 28m\Omega$ $P_{D} = 2.1W$



Packaged in the SOT89 outline this low saturation 55V NPN transistor offers extremely low on state losses making it ideal for use in DC-DC circuits and various driving and power management functions.

Feature

- Extremely low equivalent on-resistance of $28 m\Omega$
- 6 Amps continuous current
- Up to 10 amps peak current
- Very low saturation voltages
- Excellent h_{FE} characteristics up to 10 amps
- 150V Forward blocking voltage

Applications

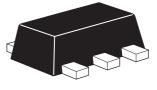
- Emergency lighting circuits
- Motor driving (including DC fans)
- · Solenoid, relay and actuator drivers
- DC modules
- · Backlight inverters

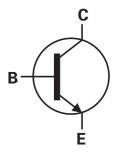
Ordering information

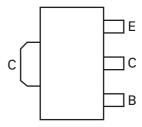
Device	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTN19055DZTA	7	12	1000

Device marking

S75







Pinout - top view

Absolute maximum ratings

Parameter	Symbol	Limit	Unit
Collector-base voltage	V _{CBO}	150	V
Collector-emitter voltage (forward blocking voltage)	V _{CEX}	150	V
Collector-emitter voltage (base open)	V _{CEO}	55	V
Emitter-base voltage	V _{EBO}	7	V
Continuous collector current ^(b)	Ι _C	6	А
Peak pulse current	I _{CM}	10	А
Power dissipation at $T_{amb} = 25^{\circ}C^{(a)}$	P _D	1.5	W
Linear derating factor		12	mW/°C
Power dissipation at $T_{amb} = 25^{\circ}C^{(b)}$	P _D	2.1	W
Linear derating factor		16.8	mW/°C
Operating and storage temperature range	T _j , T _{stg}	-55 to +150	°C

Thermal resistance

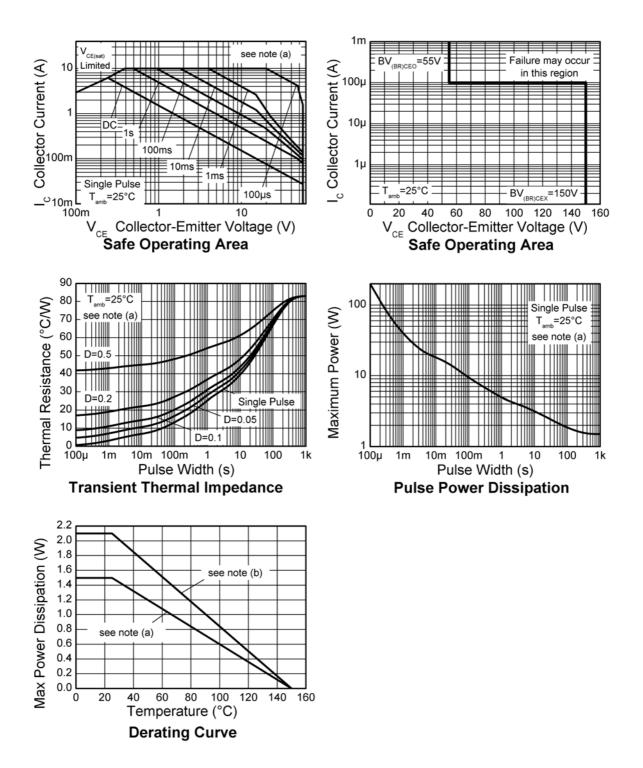
Parameter	Symbol	Limit	Unit
Junction to ambient ^(a)	R_{\ThetaJA}	83	°C/W
Junction to ambient ^(b)	R_{\ThetaJA}	59	°C/W

NOTES:

(a) For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

(b) For a device surface mounted on 50mm x 50mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

Characteristics



Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV _{CBO}	150	200		V	I _C = 100mA
Collector-emitter breakdown voltage (forward blocking)	BV _{CEX}	150	200		V	I_C = 100mA, R_{BE} < 1k Ω or -1V < V _{BE} < +0.25V
Collector-emitter breakdown voltage (base open)	BV _{CEO}	55	75		V	I _C = 10mA ^(*)
Emitter-base breakdown voltage	BV _{EBO}	7	8.1		V	IE = 100mA
Collector-base cut-off current	I _{CBO}		<1	50	nA	V _{CB} = 120V
				20	μA	$V_{CB} = 120V, T_{amb} = 100^{\circ}C$
Collector-emitter cut-off current	I _{CEX}		<1	100	nA	$\label{eq:VCE} \begin{split} &V_{CE} = 120V; R_{BE} < 1k\Omega or \\ &-1V < V_{BE} < 0.25V \end{split}$
Emitter cut-off current	I _{EBO}		<1	50	nA	V _{EB} = 5.6V
Collector-emitter saturation	V _{CE(sat)}		25	40	mV	l _C = 0.5A, l _B = 50mA ^(*)
voltage			45	70	mV	$I_{C} = 1A, I_{B} = 50mA^{(*)}$
			40	60	mV	$I_{C} = 1A, I_{B} = 100 \text{mA}^{(*)}$
			200	350	mV	I _C = 2A, I _B = 20mA ^(*)
			110	140	mV	$I_{C} = 2A, I_{B} = 40mA^{(*)}$
			140	200	mV	I _C = 4A, I _B = 200mA ^(*)
			170	250	mV	I _C = 6A, I _B = 600mA ^(*)
Base-emitter saturation	V _{BE(sat)}		800	900	mV	$I_{C} = 2A, I_{B} = 20mA^{(*)}$
voltage			1000	1150	mV	$I_{C} = 6A, I_{B} = 600 \text{mA}^{(*)}$
Base-emitter turn-on voltage	V _{BE(on)}		760	900	mV	$I_{C} = 2A, V_{CE} = 2V^{(*)}$
			900	1050	mV	$I_{C} = 6A, V_{CE} = 2V^{(*)}$
Static forward current transfer	h _{FE}	250	400	700		$I_{C} = 10 \text{mA}, V_{CE} = 2V^{(*)}$
ratio		250	400			$I_{C} = 1A, V_{CE} = 2V^{(*)}$
		180	300			$I_{C} = 2A, V_{CE} = 2V^{(*)}$
		30	50			$I_{C} = 6A, V_{CE} = 2V^{(*)}$
			20			$I_{C} = 10A, V_{CE} = 2V^{(*)}$
Transition frequency	f _T	140	200		MHz	I _C = 100mA, V _{CE} =10 V f = 50MHz
Output capacitance	C _{OBO}		21.2	30	pF	V _{CB} = 10V, f = 1MHz
Delay time	t _d		13.8			V _{CC} = 10V,
Rise time	t _r		21.9			I _C = 1A,
Storage time	t _s		546			I _{B1} = I _{B2} = 100mA
Fall time	t _f		106			

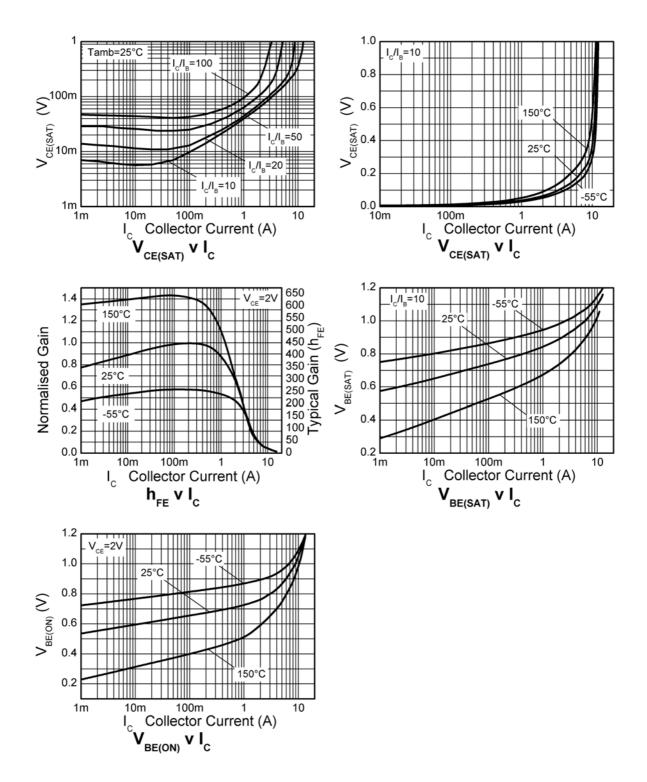
Electrical characteristics (at $T_{amb} = 25^{\circ}C$ unless otherwise stated)

NOTES:

(*) Measured under pulsed conditions. Pulse width \leq 300µs; duty cycle \leq 2%.

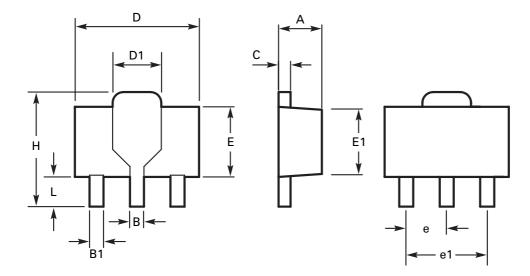
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Typical characteristics



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Package outline - SOT89



DIM	Millin	neters	Inc	hes	DIM	Millimeters		Inches	
	Min	Мах	Min	Мах		Min	Мах	Min	Max
A	1.40	1.60	0.550	0.630	E1	2.13	2.29	0.084	0.090
В	0.44	0.56	0.017	0.022	е	1.50	BSC	0.059	BSC
B1	0.36	0.48	0.014	0.019	e1	3.00 BSC		0.118 BSC	
С	0.35	0.44	0.014	0.019	Н	3.94	4.25	0.155	0.167
D	4.40	4.60	0.173	0.181	L	0.89	1.20	0.155	0.167
E	2.29	2.60	0.090	0.102		-	-	-	-

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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